

Form PTO 1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. 728-203 DIV		SERIAL NO. 10/666,972	
<div style="position: relative; height: 100px;"> <div style="position: absolute; top: 0; left: 0; width: 100%; height: 100%; border: 1px solid black; border-radius: 50%; text-align: center; line-height: 100px; font-size: 24px; font-weight: bold; transform: rotate(-45deg);"> CIPED 10/23/2003 </div> </div>				INFORMATION DISCLOSURE STATEMENT BY APPLICANT			
				(Use several sheets if necessary)		APPLICANTS Louis L. HSU, et al.	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
m		5,539,217	07/23/1996	Edmond et al.			
↓		5,742,076	04/21/1998	Sridevan et al.			
↓		5,925,895	07/20/1999	Sriram et al.			
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO
OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
m		Nemati et al, "A Novel High Density, Low Voltage SRAM Cell with a Vertical NDR Device", 1 on VLSI Technology Digest of Technical Papers, IEEE, pages 66-67, 1998.					
m		Nemati et al, "A Novel Thyristor-based SRAM Cell (T-RAM) for High Speed, Low-Voltage, Gig Memories", IEDM 1999, 283-286					
EXAMINER				DATE CONSIDERED			
* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							